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GALLIUM NITRIDE POWER ELECTRONICS IN 2025: STATUS, APPLICATIONS, AND ROADBLOCKS

L.S. Chuah[1*], **Z. R. Leong**[1, 2]
[1]Physics Section, School of Distance Education, Universiti Sains Malaysia, 11800
Penang, Malaysia.
[2] Opulent Solution Sdn. Bhd. Plot 111, Bayan Lepas Industrial Park, Lebuh Raya,
Kampung Jawa, 11900 Penang, Malaysia.
Email : chuahleesiang@usm.my

Abstract

By 2025, the power electronics based on gallium nitride (GaN) have become standardized with niche applications and mainstream applications, as the intrinsic material properties, such as high electron mobility, high breakdown voltage, and low on-resistance, have enabled this. This paper will present an overview of the present and past of GaN power electronics, device structures, applications and issue of the computer power electronics. The usage of GaN includes consumer chargers, high-density DC to DC converters, on-board chargers to power electric vehicles, and data center power systems with the global market expected to reach USD 3 billion. The most common types of devices are GaN-on-Si HEMTs, monolithic GaN Power ICs, and new vertical GaN devices to be used in high-voltage applications. The paper identifies serious technical issues, such as reliability, thermal management, packaging, parasitic effects, and automotive and industrial standardization. It also discusses the roadblocks like the manufacturing cost, design skill and ecosystem support and also finds close and mid-term opportunities to integrate the system on the system level. The results highlight the capability of GaN in supporting small, efficient, and high-performance power solutions in consumer, automotive and industrial applications.

Keywords: *GaN power devices, GaN HEMT, GaN Power IC, vertical GaN, reliability, packaging, thermal management, on-board chargers, DC–DC converters.*

1. INTRODUCTION

In 2025, Gallium Nitride (GaN) power electronics have become the groundbreaking technology in the energy conversion and electronic systems. The material properties of GaN, such as high electron mobility, large bandgap and high breakdown voltage enable the operation of devices at higher frequencies, with lower conduction losses, and much better thermal stability than silicon-based semiconductors. These properties make smaller, efficient and high-power-density designs possible, and are especially useful where size and high-power density are important, e.g. chargers of consumer electronics, data center power supplies, and auxiliary converters of electric vehicles (EVs). Their capacity to satisfy the increasing demand of smaller form factors, faster charging and enhanced energy efficiency in various sectors, has been evidenced by the ability to be commercially adopted rapidly by GaN devices.

Although there is a technological potential, mass implementation of GaN has issues of reliability, packaging and standardization. Parasitic effects, thermal management complexities and special failure modes like gate degradation and charge trapping are introduced by high-speed switching, but these failure modes are poorly understood and need to be properly designed and tested. Moreover, the question of automotive and industrial application standards, which are used in the industry, is not final and scalability of manufacture is an issue. These benefits and drawbacks are essential in the realization of the potential of many-to-many controlled power electronics using GaN and in future research and commercialization plans.

1.1.Objectives of the Study

- To examine the present state, the market dynamics, and the most important uses of gallium nitride (GaN) power electronics in 2025.
- To determine reliability, packaging and technical issues of GaN devices.
- To determine opportunities and adoption barriers of GaN technology in future.

2. LITERATURE REVIEW

De Rooij et al. (2024) explored the uses of the gallium nitride (GaN) technology in various power conversion fields. They stated that GaN devices had become commercialized devices beyond research devices to include high efficiency consumer chargers, electric vehicle (EV) auxiliary converters, and industrial power systems. The point that their research brought out was that the high-power density, small size and high frequency operation of GaN was made possible by both superior material properties; high mobility of electrons in the material, wide bandgap and novel device architectures. These characteristics offered huge performance advantages against traditional silicon-based designs such as reduced conduction and switching loss, reduced size of passive components and enhanced thermal performance.

Lin and Shen (2024) studied the intrinsic material properties of GaN specifically with regard to the physical and electrical properties that rendered it the best in next generation power electronics. They showed that GaN has a high electron mobility that facilitated the transport of charge carriers quickly and high breakdown voltage that ensured that devices operated with high operation voltages. The large bandgap led to greater thermal stability and less leakage currents that together led to lower conduction losses and greater energy efficiency. Lin and Shen have concluded that these underlying material properties were an important consideration to the design and optimization of GaN-based devices, especially in those areas which require a high-power density, rapid switching speeds, and the ability to be compact in size.

Song (2024) addressed the topic of the strength and reliability of GaN transistors in the conditions of dynamic switching of power. It has been found that, although there were high-speed and high-efficiency properties of GaN, devices tended to undergo certain failure mechanisms such as gate degradation, charge trapping at the AlGaN/GaN interface and thermal fatigue caused by repeated power cycling. Song pointed out that the problems may affect the longevity of device reliability particularly in the automotive sector as well as the high-density power systems. The study demonstrated the relevance of device designing factors including optimization of the gate structure, passivation on the surface, and advanced packaging as a means of reducing the impact of the stress. Further, Song noted the need to have strict reliability test guidelines in order to make sure that the GaN devices would be safe to use with high dv/dt levels and high temperature, even in industrial and automotive harsh conditions.

Wang (2024) explored the design, production, characterization and packaging of gallium oxide (Ga2O3) diodes as a complementary technology using wide-bandgap. The paper has highlighted the importance of packaging and thermal management in ensuring the performance of a device, especially with high voltage of operation and in high-speed switching. Wang proved that best substrate choice, thermal interface material and die-attach method were necessary to limit thermal resistance and avoid focal hotspots, which might destroy performance and dependability of the device. Ga2O3 devices had not yet reached the same level of maturity as GaN but the work did offer a good understanding of the structure of the device, how to handle high voltages safely, and how to scale up to wide-bandgap semiconductors.

3. MARKET & APPLICATION OVERVIEW (2025)

The emerging commercial development of the GaN power electronics market in 2025 is based on the natural advantages of the technology over tradition silicon. GaN offers better breakdown voltage, lower on-resistance, higher switching rate, and lower parasitic capacitance which allows smaller, efficient and high power-density designs. These are useful mostly in products where efficiency, size and temperature regulation are important like consumer chargers, onboard EV chargers, DC to DC converters, data center power systems and industrial power supplies. The subsequent sub-sections present an elaborate explanation of market size, major fields of application, and motivation of GaN use in any given segment.

1) Market Size and Growth

The worldwide ecosystem of GaN power devices, both discrete devices and integrated power ICs, has a multi-billion-dollar market in 2025, and healthy growth is expected in a variety of segments. This growth is a result of strong adoption in consumer electronics, EV power systems, and high efficiency industrial converters. According to market analyses, the overall market size of GaN will have increased to USD 3.2 billion in 2025 as compared to USD 1.95 billion in 2024 with compound growth rate (CAGR) of about 24 percent between 2024 and 2030.

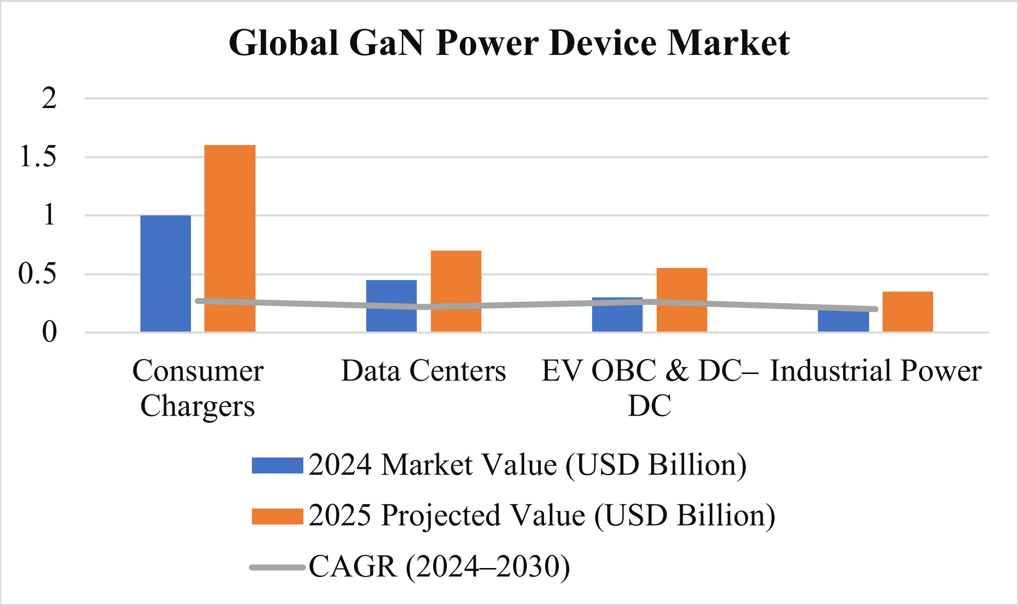

Figure 1: Global GaN Power Device Market by Application (2024–2025)

The Figure demonstrates that the most significant subsector is consumer chargers, then there are data center power solutions, and emerging EV applications. The adoption of industrial power is increasingly becoming a trend as a result of the necessity of efficient conversion of energy in automation and intelligent production.

2) Consumer Chargers

The most developed market of GaN devices is consumer electronics. Laptops, tablets and smartphones, high-wattage (65-140 W) USB Power Delivery chargers nowadays widely use GaN to allow smaller form factors, greater efficiency and increased charging speed. Anker, Belkin, Samsung, and Xiaomi are some manufacturers that exploit GaN to ensure a smaller size of components, less heat, and quick charging. By 2025, it is estimated that consumer chargers will represent up to 50 percent of all the GaN power device market.

3) EV On-Board Chargers (OBC) and DC to DC Converters.

GaN devices are now being implemented in EV OBCs as well as auxiliary DC converters to DC converters with higher power density, better thermal management and better partial-load performance. Although traction inverters continue to use SiC, the use of GaN in auxiliary converters is increasing, and may be extended to medium-voltage converters by 2027-2030.

4) Data Centers & Telecom

Intermediate bus converters and point-of-load regulators are going to use GaN instead of silicon, and the switching frequency (500 kHz2 -MHz) is going to be increased, leading to less cooling requirements, and higher power density. This makes boards smaller and lower in cost, increasing the adoption of GaN in data centers and telecommunication networks on a hyperscale basis.

4. DEVICE TYPES & INTEGRATION TRENDS

The high performance of GaN power electronics can be explained not only by its excellent material attributes, but also because of its innovative device's architecture and integration strategies. The design of devices dictates the way they will be able to handle voltages, how fast they will be able to switch and how they will be able to manage heat, and how easily they will be able to find application in other systems. GaN-on-Si high-voltage automotive and industrial applications GaN-on-Si high-voltage monolithic GaN Power ICs and monolithic heterogeneous vertical GaN devices are the most prominent types of GaN devices in 2025. This section analyzes these architectures, their technical merits, constraints and adoption.

a) GaN-on-Si HEMTs (Lateral Devices)

The 2025 commercial GaN power electronics is based on GaN-on-Si HEMTs. They are created on silicon and they use CMOS infrastructure to create cost-effective and scalable devices. The main characteristics are a voltage range of 100-650 V, high electron mobility of the 2DEG channel, and the lateral heat conduction, which must be carefully packaged. They are commonly used in discrete power modules, half-bridge modules, and co-packaged driver-FETs. Disadvantages are the inductive parasitism, heat spreading and voltage scaling above 650 V.

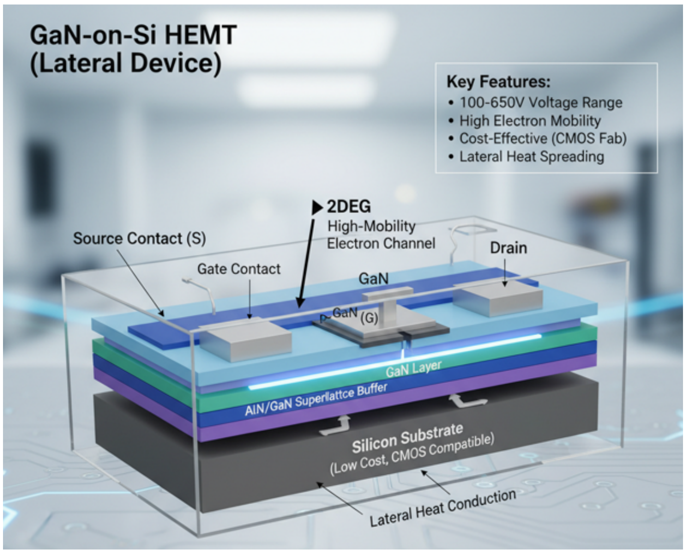

Figure 2: GaN-on-Si HEMTs (Lateral Device) Structure

b) GaN Power ICs (Monolithic Integration)

GaN Power ICs combine high-side/low-side FETs, drivers and protection circuitry on a single chip, minimizing parasitics, EMI, and board space and simplifying system design. The devices allow small high performance power stages in consumer electronics and EV auxiliary converters. The restrictions are the complexity of fabrication, cost and voltage scaling that is limited to approximately 650 V.

c) Vertical GaN Devices

Vertical GaN devices are enhanced by being able to operate at high voltages (600-1200 V) with better thermal conductivity and an increase in voltage. Early-stage adoption: EV traction inverters and industrial power system: Early-stage adoption focuses on the costs and availability of wafer-based products, but is limited by cost and wafer availability.

d) Device Comparison (2025)

Table 1 provides the summary of the key types of GaN devices as of 2025 and their characteristics, such as structure, voltage range, level of integration, benefits, and drawbacks. This analogy shows why the lateral GaN-on-Si is the dominant technology today, whereas integrated Power ICs and vertical GaN devices are the future of greater efficiency, reduced size and higher voltages.

Table 1: Comparison of Major GaN Device Types in 2025

Device Type	**Structure**	**Typical Voltage Range**	**Integration Level**	**Key Advantages**	**Limitations**
GaN-on-Si HEMT	Lateral	100–650 V	Discrete	Mature, cost-effective	Parasitic inductance, lateral heat path
GaN Power IC	Lateral Monolithic	100–650 V	High (driver + FET)	Compact, low EMI, fast switching	Complex fabrication, limited voltage scaling
Vertical GaN	Vertical	600–1200 V	Medium	High voltage, potential for traction use	Early stage, costly epitaxy

(Compiled from EPC, Infineon, and GaN Systems reports, 2025)

GaN-on-Si HEMTs are currently manufactured in large numbers in 2025 because of cost-effectiveness, GaN Power ICs are used to achieve miniaturization and integration and vertical GaN devices are used in high-voltage applications. Combined, these forms of devices characterize the present state of the field and future direction of GaN power electronics, allowing increased efficiency, reduced size, and system-level benefits both in consumer markets and automotive and industrial fields.

5. RELIABILITY, FAILURE MODES, AND QUALIFICATION

The success of GaN power electronics technologies in the long run is based not solely on the performance, but also on the reliability of the devices in the conditions of their operation. GaN devices are better in terms of switching speed and efficiency but their new material behavior raises some special reliability issues than traditional silicon MOSFETs. The importance of knowing the mechanisms of failure, stress conditions, and standardized qualification procedures is very important especially in consumer, industrial and automotive application where the safety and lifetime as well as performance stability are obligatory.

5.1. Reliability Status (2025)

GaN devices have come a long way in the reliability by the year 2025. Long-term experiments indicate that GaN-on-Si HEMTs and GaN Power ICs with a mean time to failure (MTTF) are approaching silicon MOSFETs in the use of chargers and DC-DC converters. Some of the improvements in reliability will be:

- **Gate robustness:** Passivation encasings and optimized Schottky or p-GaN gates deteriorate gate degradation.
- **Thermal stability:** With high switching frequency, advanced packaging and die attach material enhance heat dissipation.
- **Surge tolerance:** Co-packaged protection circuits and ESD diodes overcome system transients.

Nevertheless, car and EV uses are more demanding in terms of reliability over the years (such as extended temperatures, high power cycles, and sustained surge tolerance), and to these expectations, more rigorous testing procedures are necessary.

5.2.Common Failure Mechanisms

Several key failure mechanisms have been identified in GaN devices. Understanding these mechanisms is crucial for designing robust systems and improving lifetime.

Table 2: Key Reliability Challenges and Failure Mechanisms in GaN Devices

Failure Mechanism	Physical Cause	Typical Stress Condition	Mitigation Strategy
Gate degradation	Electric field stress at Schottky gate	High gate bias, elevated temperature	Gate field shaping, surface passivation
Dynamic on-resistance increase	Charge trapping at surface/interface	Switching under high dv/dt	Surface treatments, p-GaN cap
Thermal fatigue	CTE mismatch between die & substrate	Repeated power cycling	Improved packaging, sintered die attach
ESD/Surge damage	Limited protection circuit	System transients, surge events	ESD diodes, co-packaged protection

5.3.Qualification for Automotive Use

The adoption of GaN devices in the automotive sector is subject to the assumption that it fulfills or surpasses the requirement of AEC-Q101 standards. The important changes to be made to GaN are:

- **Dynamic switching tests:** Checking reliability at a high rate of frequency, high dv/dt.
- **Surge robustness:** Ranking tolerance to electrical transients found in EV systems.
- **Temperature cycling:** Evaluation under lower than 40C to higher than 150C operation.

Under these adapted standards, on-board chargers (OBC) and auxiliary converters are being tested by leading automotive OEMs including Toyota, Hyundai and Tesla. It is paramount that further standardization and the use of data over an extended period are essential to further the adoption of traction inverters.

6. PACKAGING AND THERMAL MANAGEMENT CHALLENGES

Packaging and thermal management are the key factors which have a direct influence on the performance, reliability and efficiency of GaN power devices. GaN is associated with thin layers and high switching speeds making it susceptible to performance loss through the introduction of parasitic inductance and thermal bottlenecks through traditional packaging methods. By 2025, these problems have been alleviated through serious innovation in the package design, substrate materials and thermal interface engineering, allowing more compact power modules with high frequency and high power density and robustness.

6.1. Parasitics and Switching Performance

Electromagnetic interference (EMI), voltage overshoot and ringing, and greater stress on gate drivers and lower circuitry are some of the challenges that may be experienced when switching at high speed in GaN devices. To address them, package designs with low inductance have become the standard such as flip-chip BGA (Ball Grid Array) to reduce the loop inductance, packages made of embedded dies, directly printed into PCB substrates, and dual-side cooled modules that support active thermal management with high switching performance. This kind of optimized package improves the performance of electrical systems, increases life cycle of device and reliability of a system as a whole.

6.2.Thermal Pathways

Lateral GaN-on-Si devices have a critical thermal management because heat is primarily laterally conducted via the silicon substrate causing prospective hotspots in densities with high switching. The major plans to be made in 2025 were direct-bond copper (DBC) substrates to achieve high thermal conductivity, improved thermal interface materials (TIMs) to minimize contact resistance, and heat-spreading copper planes in dual side cooling to ensure safe junction temperatures. These designs guaranteed steady RDS (on), reduced switching losses, and increased device life, particularly in high-frequency or high-power cycling of the devices in EV and industrial environments.

7. STANDARDS, TESTING & QUALIFICATION

With the move of GaN power electronics to mainstream use especially in automotive, industrial, and telecom applications, harmonization of standards, test procedures and qualification processes is urgent. GaN devices, in contrast to silicon MOSFETs, have their own failure modes, rapid switching characteristics and thermal issues, and they require specific test plans. Standardization offers reliability, interoperability and confidence of OEMs adoption, faster commercialization and a lower risk of system integration.

Current Efforts in GaN Qualification

The industry organizations have identified the strong necessity of stable GaN testing schemes by 2025:

1. **Power Sources Manufacturers Association (PSMA):** PSMA has been working with devices manufacturers on developing GaN specific qualification criteria that cover high dv/dt stress, thermal cycling and surge robustness.
2. **JEDEC Solid State Technology Association:** JEDEC is modifying the established semiconductor tests of reliability to GaN, such as high-frequency switching endurance, dynamic Rds(on)stability, and transient tolerance tests.
3. **AEC-Q Adaptation:** GA N AEC-Q101 is being piloted by Automotive OEMs to support these modifications: dynamic switching tests, temperature cycling, and surge robustness AEC-Q would make automotive OEMs suitable as EV on-board chargers (OBCs) and auxiliary converters.

Critical Goal: Design internationally accepted standards of GaN qualification that consolidate the testing of consumer, automotive, industrial and high-voltage.

8. ROADBLOCKS TO WIDER ADOPTION

Although the power devices of the GaN type have obvious performance and efficiency benefits, there are a number of technical, economic and ecosystem-related barriers that do not allow the large-scale application of power gadgets. These checkpoints affect the cost, reliability, packaging and design feasibility and need to be dealt with by coordinated research, standardization and inter-industry cooperation.

Table 3: Summary of Roadblocks to GaN Power Electronics Adoption

Category	Description	Impact	Mitigation Path
Manufacturing Cost	Limited 300 mm wafer yield and scaling	Medium–High	Scale up wafer size, process standardization
Reliability & Standards	Lack of unified qualification (AEC-Q for GaN)	High	Develop JEDEC/PSMA standard
Packaging Integration	EMI, parasitic inductance	Medium	Integrated packages, co-design tools
Design Expertise	Lack of GaN-specific design experience	Medium	Training, reference designs
Ecosystem Support	Incomplete foundry and supply chain	Medium	Strengthen partnerships, open PDKs

1. **Manufacturing Cost:** GaN on Si remains limited to a wafer yield especially on larger sizes (200-300 mm). GaN can compete with silicon in high-volume applications due to scaling up to production and making processes standardized to be cost per device.
2. **Reliability & Standards:** The lack of standardized qualification confusingly affects OEMs especially in automotive and industrial industries. Wider adoption requires development of standardized testing protocols via the JEDEC, PSMA and AEC-Q adaptation.

3. **Challenges of Packaging Integration:** GaN switching is fast creating EMI and parasitic inductance, which might affect the performance of the system level. To eliminate such problems innovative packaging techniques like flip-chip BGA, embedded die and co-packed module, co-design tools are needed.
4. **Design Expertise:** Design of GaN devices involves expert design skills, such as design of gate drive, thermal design and layout design optimization. Training programs, reference designs, and application notes should be industry-wide so as to prepare the engineers to work with GaN integration.
5. **Ecosystem Support:** An entire GaN ecosystem such as foundries, test facilities, design kits (PDKs), and supply chains continues to develop. Enhancing the relationships with partners, allowing open-access design tools, and building a strong supply chain are essential towards increasing adoption.

9. OPPORTUNITIES & FUTURE DIRECTIONS

As the field of GaN power electronics keeps developing, there is increasing prospect with a variety of opportunities in different time horizons. These opportunities are stimulated by the special opportunities of GaN such as high switching speed, low conduction losses and great power density. GaN devices could be in a good position to satisfy the increasing needs of consumer electronics, electric vehicles, data centers, and industrial power systems by enabling smaller, optimized, and thermally efficient power solutions. The insight into the near and mid-term trends allows tracing the development of this technology and its commercial implementation.

- **Near-Term Opportunities (2025-2027):** GaN is targeted into rhyme of high efficiency, compactness and thermal performance of applications. The high switching speeds, reduced form factor, and reduced heat generation of GaN are capturing the attention of high-wattage USB Power Delivery chargers, high-density DC -DC converters in data centers and telecom, and EV on-board chargers (OBCs). Such applications will see improved speed as OEMs incorporate the components of the GaN into mass-manufactured products and EV models.
- **Mid-Term Opportunities (2027-2030):** It is anticipated that GaN will extend into higher voltages and system-levels using vertical GaN devices and solutions which are co-packaged. Vertical GaN devices with a maximum of 1200 V are appropriate in EV traction inverters and high-power industrial drives, and they are smaller and more efficient. Co-packaged solutions combine drivers, controllers, and protection circuits, reducing parasitics and improving EMI behavior and provide an easier approach to system design, a move towards complete system-level integration.

10. CONCLUSION

GaN power electronics has taken root as a disruptive technology in the field of energy-efficient power conversion by 2025, especially in consumer electronics, auxiliary systems in electric vehicles and in densely populated industrial environments. High material characteristics, along with new device architectures of GaN-on-Si HEMTs, monolithic GaN Power ICs, and vertical GaN devices, have made better efficiency, faster switching, and designs smaller. Although much has been achieved, there are still difficulties in scalability of manufacturing, thermal regulation, minimization of parasitics and in cohesive reliability criteria and particularly with high-voltage industrial and automotive use. These roadblocks will be overcome by industry collaboration, standardization and design innovation that will be important in broader adoption. With the maturity of the GaN technology, it is hoped that integrating the technology into system-level solutions will transform the face of power electronics because of the high-performance, miniature, and energy-efficient devices are becoming available, making GaN a key enabler of next-generation electrified systems in consumer, automotive, and industrial applications.

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